

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

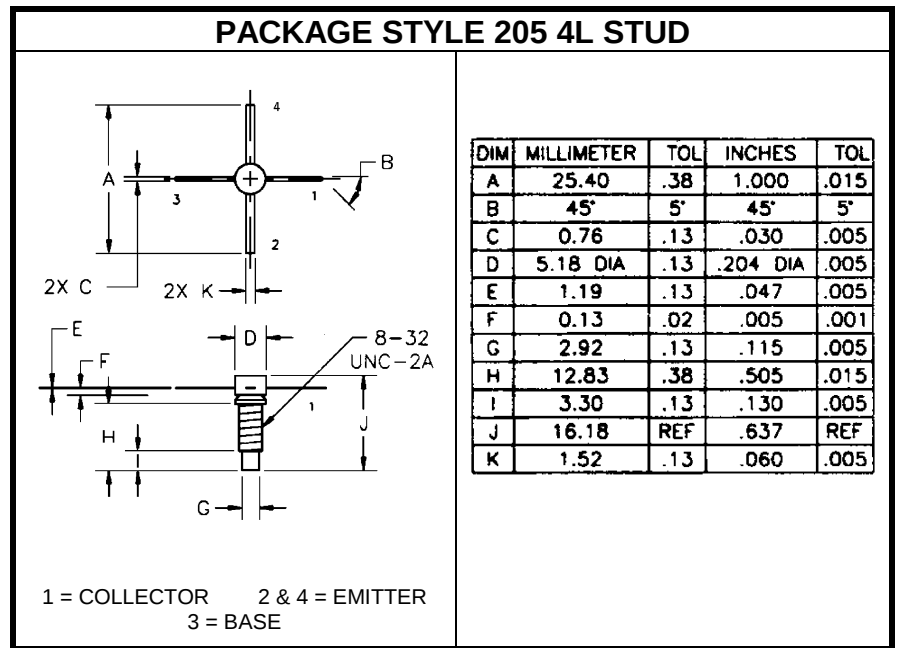
The **ASI BLV99** is a Common Emitter Device Designed for Amplifier Applications up to 860 MHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	300 mA
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	5.3 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	33°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CBO}	I _C = 1.0mA			45			V
BV _{CER}	I _C = 10 mA	R _{BE} = 10 Ω		45			V
BV _{EBO}	I _E = 1.0 mA			3.5			V
I _{CBO}	V _{EB} = 5.0 V					1.0	mA
h _{FE}	V _{CE} = 5 V	I _C = 100 mA		20			---
C _{OB}	V _{CB} = 24 V						